Welcome to E-XFL.COM

What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	-
Core Size	-
Speed	-
Connectivity	-
Peripherals	-
Number of I/O	-
Program Memory Size	-
Program Memory Type	-
EEPROM Size	-
RAM Size	-
Voltage - Supply (Vcc/Vdd)	-
Data Converters	-
Oscillator Type	-
Operating Temperature	-
Mounting Type	-
Package / Case	-
Supplier Device Package	-
Purchase URL	https://www.e-xfl.com/product-detail/infineon-technologies/cyshm35926p-l068lti

Contents

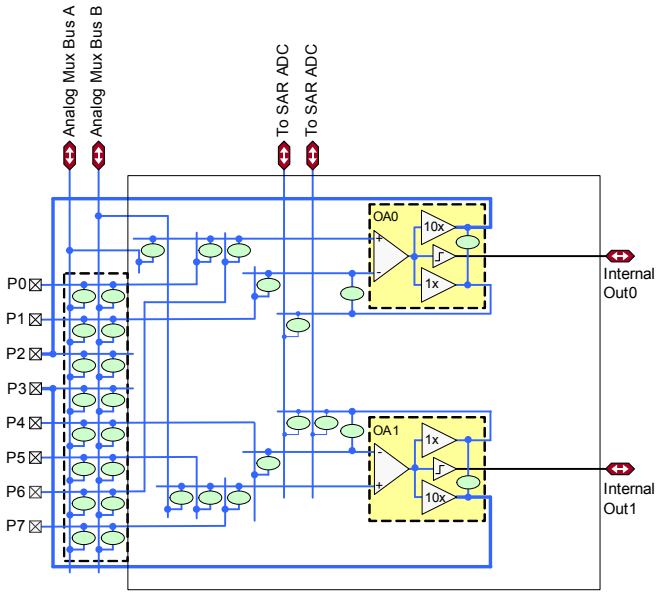
Analog Multiplex Bus

The SHM 35920-L has two concentric analog buses (Analog Mux Bus A and Analog Mux Bus B) that circumnavigate the periphery of the chip. These buses can transport analog signals from any pin to various analog blocks (including the opamps) allowing, for example, the ADC to monitor any pin on the chip. These buses are independent and can also be split into three independent sections. This allows one section to be used for general analog signal processing, and one for general-purpose digital peripherals and GPIO.

Four Opamps (CTBm Blocks)

The SHM 35920-L has four opamps with Comparator modes, which allow most common analog functions to be performed on-chip eliminating external components; PGAs, voltage buffers, filters, trans-impedance amplifiers, and other functions can be realized with external passives saving power, cost, and space. The on-chip opamps are designed with enough bandwidth to drive the Sample-and-Hold circuit of the ADC without requiring external buffering. The opamps can operate in the Deep Sleep mode at very low power levels. The following diagram shows one of two identical opamp pairs of the opamp subsystem.

Figure 4. Identical Opamp Pairs in Opamp Subsystem



The ovals in Figure 4 represent analog switches, which may be controlled via user firmware, the SAR sequencer, or user-defined programmable logic. The opamps (OA0 and OA1) are configurable via these switches to perform all standard opamp functions with appropriate feedback components.

The opamps (OA0 and OA1) are programmable and reconfigurable to provide standard opamp functionality via switchable feedback components, unity gain functionality for driving pins directly, or for internal use (such as buffering SAR ADC inputs as indicated in the diagram), or as true comparators.

The opamp inputs provide highly flexible connectivity and can connect directly to dedicated pins or, via the analog mux buses, to any pin on the chip. Analog switch connectivity is controllable by user firmware as well as user-defined programmable digital state machines (implemented via UDBs).

The opamps operate in Deep Sleep mode at very low currents allowing analog circuits to remain operational during Deep Sleep.

Temperature Sensor

The SHM 35920-L has one on-chip temperature sensor. This consists of a diode, which is biased by a current source that can be disabled to save power. The temperature sensor is connected to the ADC, which digitizes the reading and produces a temperature value using Cypress-supplied software that includes calibration and linearization.

Low-power Comparators

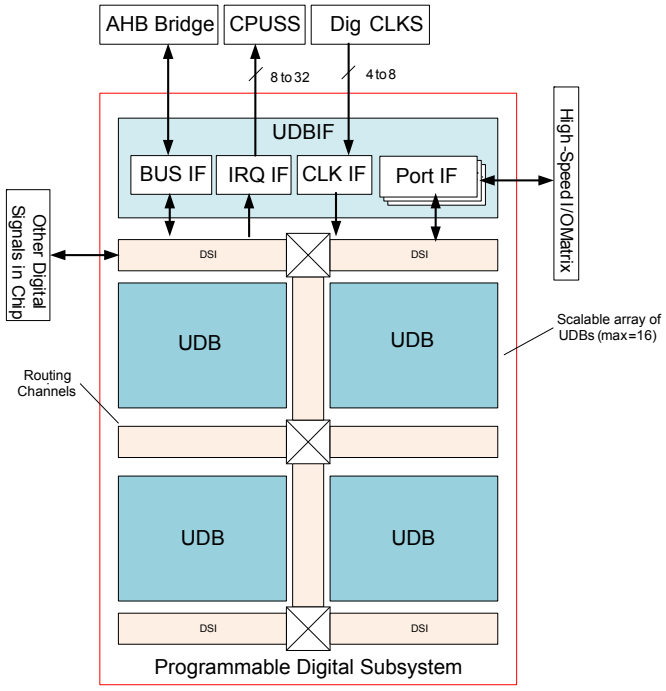
The SHM 35920-L has a pair of low-power comparators, which can also operate in the Deep Sleep and Hibernate modes. This allows the analog system blocks to be disabled while retaining the ability to monitor external voltage levels during low-power modes. The comparator outputs are normally synchronized to avoid meta-stability unless operating in an asynchronous power mode (Hibernate) where the system wake-up circuit is activated by a comparator switch event.

Programmable Digital

Universal Digital Blocks (UDBs) and Port Interfaces

The SHM 35920-L has eight UDBs; the UDB array also provides a switched Digital System Interconnect (DSI) fabric that allows signals from peripherals and ports to be routed to and through the UDBs for communication and control. The UDB array is shown in the following figure.

Figure 5. UDB Array



Pinouts

The following is the pin list for the SHM 35920-L.

68-QFN		68-QFN	
Pin	**Name**	**Pin**	**Name**
1	P1.7/VREF	35	P4.7
2	P2.0	36	D+/P13.0
3	P2.1	37	D-/P13.1
4	P2.2	38	VBUS/P13.2
5	P2.3	39	P7.0
6	P2.4	40	P7.1
7	P2.5	41	P7.2
8	P2.6	42	P0.0
9	P2.7	43	P0.1
10	VSSA	44	P0.2
11	VDDA	45	P0.3
12	P6.0	46	P0.4
13	P6.1	47	P0.5
14	P6.2	48	P0.6
15	P6.3	49	P0.7
16	P6.4/P12.0	50	XRES
17	P6.5/P12.1	51	VCCD
18	VSSIO	52	VSSD
19	P3.0	53	VDDD
20	P3.1	54	P5.0
21	P3.2	55	P5.1
22	P3.3	56	P5.2
23	P3.4	57	P5.3
24	P3.5	58	P5.4
25	P3.6	59	P5.5
26	P3.7	60	VDDA
27	VDDIO	61	VSSA
28	P4.0	62	P1.0
29	P4.1	63	P1.1
30	P4.2	64	P1.2
31	P4.3	65	P1.3
32	P4.4	66	P1.4
33	P4.5	67	P1.5
34	P4.6	68	P1.6

Port 12 (Port pins 12.0 and 12.1) are SIO pins.

Ports 6 (Port pins P6.0..6.5) are overvoltage tolerant (GPIO_OVT).

Note: P6.4/P12.0 and P6.5/P12.1 are shorted together internally to provide backward compatibility with SHM35920-M devices. PSoC Creator allows the relevant pin to be enabled based on desired SIO or GPIO_OVT functionality.

Port/Pin	Analog	PRGIO & USB	Alt. Function 1	Alt. Function 2	Alt. Function 3	Alt. Function 4	Alt. Function 5
P12.0			tcpwm.line[7]:0			scb[1].i2c_scl:3	scb[3].spi_select3:1
P12.1			tcpwm.line_compl[7]:0			scb[1].i2c_sda:3	
P3.0			tcpwm.line[0]:0	scb[1].uart_rx:2		scb[1].i2c_scl:2	scb[1].spi_mosi:2
P3.1			tcpwm.line_compl[0]:0	scb[1].uart_tx:2		scb[1].i2c_sda:2	scb[1].spi_miso:2
P3.2			tcpwm.line[1]:0	scb[1].uart_cts:2		cpuss.swd_data:0	scb[1].spi_clk:2
P3.3			tcpwm.line_compl[1]:0	scb[1].uart_rts:2		cpuss.swd_clk:0	scb[1].spi_select0:2
P3.4			tcpwm.line[2]:0				scb[1].spi_select1:1
P3.5			tcpwm.line_compl[2]:0				scb[1].spi_select2:1
P3.6			tcpwm.line[3]:0				scb[1].spi_select3:1
P3.7			tcpwm.line_compl[3]:0				
P4.0				scb[0].uart_rx:2	can[0].can_rx:1	scb[0].i2c_scl:2	scb[0].spi_mosi:2
P4.1				scb[0].uart_tx:2	can[0].can_tx:1	scb[0].i2c_sda:2	scb[0].spi_miso:2
P4.2	csd[0].c_mod			scb[0].uart_cts:2	can[0].can_tx_enb_n:1	lpcomp.comp[0]:2	scb[0].spi_clk:2
P4.3	csd[0].c_sh_tank			scb[0].uart_rts:2		lpcomp.comp[1]:2	scb[0].spi_select0:2
P4.4					can[1].can_tx_enb_n:1		scb[0].spi_select1:2
P4.5					can[1].can_rx:1		scb[0].spi_select2:2
P4.6					can[1].can_tx:1		scb[0].spi_select3:2
P4.7							
P13.0		USBDP					
P13.1		USBDM					
P13.2		VBUS					
P7.0	srss.eco_in		tcpwm.line[0]:3	scb[3].uart_rx:2		scb[3].i2c_scl:2	scb[3].spi_mosi:2
P7.1	srss.eco_out		tcpwm.line_compl[0]:3	scb[3].uart_tx:2		scb[3].i2c_sda:2	scb[3].spi_miso:2
P7.2			tcpwm.line[1]:3	scb[3].uart_cts:2			scb[3].spi_clk:2

Descriptions of the power pin functions are as follows:

VDDD: Power supply for both analog and digital sections (where there is no V_{DDA} pin)

VDDA: Analog V_{DD} pin where package pins allow; shorted to V_{DDD} otherwise

VDDIO: I/O pin power domain

VSSA: Analog ground pin where package pins allow; shorted to VSS otherwise

VSS: Ground pin

VCCD: Regulated digital supply (1.8 V ±5%)

The following package is supported: 68-pin QFN.

Power

The supply voltage range is 1.71 V to 5.5 V with all functions and circuits operating over that range.

The SHM 35920-L family allows two distinct modes of power supply operation: Unregulated External Supply and Regulated External Supply modes.

Unregulated External Supply

In this mode, the SHM 35920-L is powered by an External Power Supply that can be anywhere in the range of 1.8 V to 5.5 V. This range is also designed for battery-powered operation, for instance, the chip can be powered from a battery system that starts at 3.5 V and works down to 1.8 V. In this mode, the internal regulator of the SHM 35920-L supplies the internal logic and the VCCD output of the SHM 35920-L must be bypassed to ground via an external Capacitor (in the range of 1 to 1.6 µF; X5R ceramic or better).

VDDA and VDDD must be shorted together on the PC board; the grounds, VSSA and VSS must also be shorted together. Bypass capacitors must be used from VDDD and VDDA to ground, typical practice for systems in this frequency range is to use a capacitor in the 1 µF range in parallel with a smaller capacitor (0.1 µF, for example). Note that these are simply rules of thumb and that, for critical applications, the PCB layout, lead inductance, and the bypass capacitor parasitic should be simulated to design and obtain optimal bypassing.

Power Supply	Bypass Capacitors
VDDD–VSS and VDDIO-VSS	0.1 µF ceramic at each pin plus bulk capacitor 1 to 10 µF.
VDDA–VSSA	0.1 µF ceramic at pin. Additional 1 µF to 10 µF bulk capacitor
VCCD–VSS	1 µF ceramic capacitor at the VCCD pin
VREF–VSSA (optional)	The internal bandgap may be bypassed with a 1 µF to 10 µF capacitor for better ADC performance.

Regulated External Supply

In this mode, the SHM 35920-L is powered by an external power supply that must be within the range of 1.71 V to 1.89 V (1.8 ±5%); note that this range needs to include power supply ripple. In this mode, the VCCD and VDDD pins are shorted together and bypassed. The internal regulator is disabled in firmware.

Electrical Specifications

Absolute Maximum Ratings

Table 1. Absolute Maximum Ratings[1]

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID1	V_{DD_ABS}	Analog or digital supply relative to V_{SS} (V_{SSD} = V_{SSA})	–0.5	–	6	V	Absolute maximum
SID2	V_{CCD_ABS}	Direct digital core voltage input relative to V_{SSD}	–0.5	–	1.95	V	Absolute maximum
SID3	V_{GPIO_ABS}	GPIO voltage; V_{DDD} or V_{DDA}	–0.5	–	V_{DD}+0.5	V	Absolute maximum
SID4	I_{GPIO_ABS}	Current per GPIO	–25	–	25	mA	Absolute maximum
SID5	$I_{G\text{-}PIO\_injection}$	GPIO injection current per pin	–0.5	–	0.5	mA	Absolute maximum
BID44	ESD_HBM	Electrostatic discharge human body model	2200	–	–	V	
BID45	ESD_CDM	Electrostatic discharge charged device model	500	–	–	V	
BID46	LU	Pin current for latch-up	–140	–	140	mA	

Device Level Specifications

All specifications are valid for -40 °C ≤ TA ≤ 85 °C and TJ ≤ 100 °C, except where noted. Specifications are valid for 1.71 V to 5.5 V, except where noted.

Table 2. DC Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details / Conditions
SID53	V_{DDD}	Power Supply Input Voltage (V_{DDA} = V_{DDD} = V_{DD})	1.8	–	5.5	V	With regulator enabled
SID255	V_{DDD}	Power supply input voltage unregulated	1.71	1.8	1.89	V	Internally unregulated Supply
SID54	V_{CCD}	Output voltage (for core logic)	–	1.8	–	V	
SID55	C_{EFC}	External regulator voltage bypass	1	1.3	1.6	µF	X5R ceramic or better
SID56	C_{EXC}	Power supply decoupling capacitor	–	1	–	µF	X5R ceramic or better
Active Mode							
SID6	I_{DD1}	Execute from flash; CPU at 6 MHz	–	2.2	3.1	mA	
SID7	I_{DD2}	Execute from flash; CPU at 12 MHz	–	3.7	4.8	mA	
SID8	I_{DD3}	Execute from flash; CPU at 24 MHz	–	6.7	8.0	mA	
SID9	I_{DD4}	Execute from flash; CPU at 48 MHz	–	12.8	14.5	mA	
Sleep Mode							
SID21	I_{DD16}	I^2C wakeup, WDT, and Comparators on. Regulator Off.	–	1.8	2.2	mA	V_{DD} = 1.71 to 1.89, 6 MHz
SID22	I_{DD17}	I^2C wakeup, WDT, and Comparators on.	–	1.7	2.1	mA	V_{DD} = 1.8 to 5.5, 6 MHz

Note
1. Usage above the absolute maximum conditions listed in Table 1 may cause permanent damage to the device. Exposure to absolute maximum conditions for extended periods of time may affect device reliability. The maximum storage temperature is 150 °C in compliance with JEDEC Standard JESD22-A103, High Temperature Storage Life. When used below absolute maximum conditions but above normal operating conditions, the device may not operate to specification.

GPIO

Table 4. GPIO DC Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID57	V_{IH}[2]	Input voltage high threshold	0.7 × V_{DDD}	–	–	V	CMOS Input
SID57A	I_{IHS}	Input current when Pad > V_{DDIO} for OVT inputs	–	–	10	µA	Per I^2C Spec
SID58	V_{IL}	Input voltage low threshold	–	–	0.3 × V_{DDD}	V	CMOS Input
SID241	V_{IH}[2]	LVTTL input, V_{DDD} < 2.7 V	0.7× V_{DDD}	–	–	V	
SID242	V_{IL}	LVTTL input, V_{DDD} < 2.7 V	–	–	0.3 × V_{DDD}	V	
SID243	V_{IH}[2]	LVTTL input, $V_{DDD} \geq 2.7$ V	2.0	–	–	V	
SID244	V_{IL}	LVTTL input, $V_{DDD} \geq 2.7$ V	–	–	0.8	V	
SID59	V_{OH}	Output voltage high level	V_{DDD} –0.6	–	–	V	I_{OH} = 4 mA at 3 V V_{DDD}
SID60	V_{OH}	Output voltage high level	V_{DDD} –0.5	–	–	V	I_{OH} = 1 mA at 1.8 V V_{DDD}
SID61	V_{OL}	Output voltage low level	–	–	0.6	V	I_{OL} = 4 mA at 1.8 V V_{DDD}
SID62	V_{OL}	Output voltage low level	–	–	0.6	V	I_{OL} = 8 mA at 3 V V_{DDD}
SID62A	V_{OL}	Output voltage low level	–	–	0.4	V	I_{OL} = 3 mA at 3 V V_{DDD}
SID63	R_{PULLUP}	Pull-up resistor	3.5	5.6	8.5	kΩ	
SID64	$R_{PULLDOWN}$	Pull-down resistor	3.5	5.6	8.5	kΩ	
SID65	I_{IL}	Input leakage current (absolute value)	–	–	2	nA	25 °C, V_{DDD} = 3.0 V
SID65A	I_{IL_CTBM}	Input leakage current (absolute value) for CTBM pins	–	–	4	nA	
SID66	C_{IN}	Input capacitance	–	–	7	pF	Not applicable for P6.4, P6.5, P12.0, P12.1, and for USB pins.
SID67	V_{HYSTTL}	Input hysteresis LVTTL	25	40	–	mV	$V_{DDD} \geq 2.7$ V
SID68	$V_{HYSCMOS}$	Input hysteresis CMOS	0.05 × V_{DDD}	–	–	mV	
SID69	I_{DIODE}	Current through protection diode to V_{DD}/Vss	–	–	100	µA	Guaranteed by characterization
SID69A	I_{TOT_GPIO}	Maximum Total Source or Sink Chip Current	–	–	200	mA	Guaranteed by characterization

Note
2. V_{IH} must not exceed V_{DDD} + 0.2 V.

Table 5. GPIO AC Specifications

(Guaranteed by Characterization)[3]

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID70	T_{RISEF}	Rise time in fast strong mode	2	–	12	ns	3.3 V V_{DDD}, Cload = 25 pF
SID71	T_{FALLF}	Fall time in fast strong mode	2	–	12	ns	3.3 V V_{DDD}, Cload = 25 pF
SID72	T_{RISES}	Rise time in slow strong mode	10	–	60	ns	3.3 V V_{DDD}, Cload = 25 pF
SID73	T_{FALLS}	Fall time in slow strong mode	10	–	60	ns	3.3 V V_{DDD}, Cload = 25 pF
SID74	$F_{GPIOUT1}$	GPIO Fout;3.3 V ≤ V_{DDD} ≤ 5.5 V. Fast strong mode.	–	–	33	MHz	90/10%, 25 pF load, 60/40 duty cycle
SID75	$F_{GPIOUT2}$	GPIO Fout;1.7 V≤ V_{DDD}≤ 3.3 V. Fast strong mode.	–	–	16.7	MHz	90/10%, 25 pF load, 60/40 duty cycle
SID76	$F_{GPIOUT3}$	GPIO Fout;3.3 V ≤ V_{DDD} ≤ 5.5 V. Slow strong mode.	–	–	7	MHz	90/10%, 25 pF load, 60/40 duty cycle
SID245	$F_{GPIOUT4}$	GPIO Fout;1.7 V ≤ V_{DDD} ≤ 3.3 V. Slow strong mode.	–	–	3.5	MHz	90/10%, 25 pF load, 60/40 duty cycle
SID246	F_{GPIOIN}	GPIO input operating frequency; 1.71 V ≤ V_{DDD} ≤ 5.5 V	–	–	48	MHz	90/10% V_{IO}

XRES

Table 6. XRES DC Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID77	V_{IH}	Input voltage high threshold	0.7 × V_{DDD}	–	–	V	CMOS Input
SID78	V_{IL}	Input voltage low threshold	–	–	0.3 × V_{DDD}	V	CMOS Input
SID79	R_{PULLUP}	Pull-up resistor	3.5	5.6	8.5	kΩ	
SID80	C_{IN}	Input capacitance	–	3	–	pF	
SID81	$V_{HYSXRES}$	Input voltage hysteresis	–	100	–	mV	Guaranteed by characterization
SID82	I_{DIODE}	Current through protection diode to V_{DDD}/V_{SS}	–	–	100	µA	Guaranteed by characterization

Table 7. XRES AC Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID83	$T_{RESETWIDTH}$	Reset pulse width	1	–	–	µs	Guaranteed by characterization

Note

3. Simultaneous switching transitions on many fully-loaded GPIO pins may cause ground perturbations depending on several factors including PCB and decoupling capacitor design. For applications that are very sensitive to ground perturbations, the slower GPIO slew rate setting may be used.

Table 8. Opamp Specifications

(Guaranteed by Characterization) *(continued)*

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID_DS_17	VOS_MED_M2	Mode 2, Medium current	–	5	–	mV	With trim 25 °C, 0.2 V to V_{DDA}-1.5 V
SID_DS_18	VOS_LOW_M2	Mode 2, Low current	–	5	–	mV	With trim 25 °C, 0.2 V to V_{DDA}-1.5 V
SID_DS_19	IOUT_HI_M!	Mode 1, High current	–	10	–	mA	Output is 0.5 V to V_{DDA}-0.5 V
SID_DS_20	IOUT_MED_M1	Mode 1, Medium current	–	10	–	mA	Output is 0.5 V to V_{DDA}-0.5 V
SID_DS_21	IOUT_LOW_M1	Mode 1, Low current	–	4	–	mA	Output is 0.5 V to V_{DDA}-0.5 V
SID_DS_22	IOUT_HI_M2	Mode 2, High current	–	1	–	mA	Output is 0.5 V to V_{DDA}-0.5 V
SID_DS_23	IOU_MED_M2	Mode 2, Medium current	–	1	–	mA	Output is 0.5 V to V_{DDA}-0.5 V
SID_DS_24	IOU_LOW_M2	Mode 2, Low current	–	0.5	–	mA	Output is 0.5 V to V_{DDA}-0.5 V

Comparator

Table 9. Comparator DC Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID85	$V_{OFFSET2}$	Input offset voltage. Custom trim. Common mode voltage range from 0 to V_{DD}-1.	–	–	±4	mV	
SID85A	$V_{OFFSET3}$	Input offset voltage. Ultra low-power mode.	–	±12	–	mV	V_{DDD} ≥ 2.2 V for Temp < 0 °C, V_{DDD} ≥ 1.8 V for Temp > 0 °C
SID86	V_{HYST}	Hysteresis when enabled. Common mode voltage range from 0 to V_{DD} -1.	–	10	35	mV	Guaranteed by characterization
SID87	V_{ICM1}	Input common mode voltage in normal mode	0	–	V_{DDD} – 0.2	V	Modes 1 and 2.
SID247	V_{ICM2}	Input common mode voltage in low power mode	0	–	V_{DDD}	V	
SID247A	V_{ICM2}	Input common mode voltage in ultra low power mode	0	–	V_{DDD} – 1.15	V	V_{DDD} ≥ 2.2 V for Temp < 0 °C, V_{DDD} ≥ 1.8 V for Temp > 0 °C
SID88	CMRR	Common mode rejection ratio	50	–	–	dB	V_{DDD} ≥ 2.7 V. Guaranteed by characterization
SID88A	CMRR	Common mode rejection ratio	42	–	–	dB	V_{DDD} < 2.7 V. Guaranteed by characterization
SID89	I_{CMP1}	Block current, normal mode	–	280	400	µA	Guaranteed by characterization
SID248	I_{CMP2}	Block current, low power mode	–	50	100	µA	Guaranteed by characterization
SID259	I_{CMP3}	Block current, ultra low power mode	–	6	28	µA	Guaranteed by characterization, V_{DDD} ≥ 2.2 V for Temp < 0 °C, V_{DDD} ≥ 1.8 V for Temp > 0 °
SID90	Z_{CMP}	DC input impedance of comparator	35	–	–	MΩ	Guaranteed by characterization

Table 10. Comparator AC Specifications

(Guaranteed by Characterization)

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID91	T_{RESP1}	Response time, normal mode	–	38	110	ns	50-mV overdrive
SID258	T_{RESP2}	Response time, low power mode	–	70	200	ns	50-mV overdrive
SID92	T_{RESP3}	Response time, ultra low power mode	–	2.3	15	µs	200-mV overdrive. $V_{DDD} \geq$ 2.2 V for Temp < 0 °C, $V_{DDD} \geq$ 1.8 V for Temp > 0 °C

Temperature Sensor

Table 11. Temperature Sensor Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID93	$T_{SENSACC}$	Temperature sensor accuracy	–5	±1	+5	°C	–40 to +85 °C

SAR ADC

Table 12. SAR ADC DC Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID94	A_RES	Resolution	–	–	12	bits	
SID95	A_CHNIS_S	Number of channels - single ended	–	–	16		8 full speed
SID96	A-CHNKS_D	Number of channels - differential	–	–	8		Diff inputs use neighboring I/O
SID97	A-MONO	Monotonicity	–	–	–		Yes. Based on characterization
SID98	A_GAINERR	Gain error	–	–	±0.1	%	With external reference.
SID99	A_OFFSET	Input offset voltage	–	–	2	mV	Measured with 1-V $V_{REF.}$
SID100	A_ISAR	Current consumption	–	–	1	mA	
SID101	A_VINS	Input voltage range - single ended	V_{SS}	–	V_{DDA}	V	Based on device characterization
SID102	A_VIND	Input voltage range - differential	V_{SS}	–	V_{DDA}	V	Based on device characterization
SID103	A_INRES	Input resistance	–	–	2.2	KΩ	Based on device characterization
SID104	A_INCAP	Input capacitance	–	–	10	pF	Based on device characterization

Table 13. SAR ADC AC Specifications

(Guaranteed by Characterization)

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID106	A_PSRR	Power supply rejection ratio	70	–	–	dB	
SID107	A_CMRR	Common mode rejection ratio	66	–	–	dB	Measured at 1 V
SID108	A_SAMP_1	Sample rate with external reference bypass cap	–	–	1	Msps	
SID108A	A_SAMP_2	Sample rate with no bypass cap. Reference = V_{DD}	–	–	500	Ksps	
SID108B	A_SAMP_3	Sample rate with no bypass cap. Internal reference	–	–	100	ksps	

Digital Peripherals

The following specifications apply to the Timer/Counter/PWM peripheral in timer mode.

Timer/Counter/PWM

Table 15. TCPWM Specifications

(Guaranteed by Characterization)

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID.TCPWM.1	ITCPWM1	Block current consumption at 3 MHz	–	–	45	µA	All modes (Timer/Counter/PWM)
SID.TCPWM.2	ITCPWM2	Block current consumption at 12 MHz	–	–	155	µA	All modes (Timer/Counter/PWM)
SID.TCPWM.2A	ITCPWM3	Block current consumption at 48 MHz	–	–	650	µA	All modes (Timer/Counter/PWM)
SID.TCPWM.3	TCPWMFREQ	Operating frequency	–	–	Fc	MHz	Fc max = Fcpu. Maximum = 48 MHz
SID.TCPWM.4	TPWMENEXT	Input Trigger Pulse Width for all Trigger Events	2/Fc	–	–	ns	Trigger Events can be Stop, Start, Reload, Count, Capture, or Kill depending on which mode of operation is selected.
SID.TCPWM.5	TPWMEXT	Output Trigger Pulse widths	2/Fc	–	–	ns	Minimum possible width of Overflow, Underflow, and CC (Counter equals Compare value) trigger outputs
SID.TCPWM.5A	TCRES	Resolution of Counter	1/Fc	–	–	ns	Minimum time between successive counts
SID.TCPWM.5B	PWMRES	PWM Resolution	1/Fc	–	–	ns	Minimum pulse width of PWM Output
SID.TCPWM.5C	QRES	Quadrature inputs resolution	1/Fc	–	–	ns	Minimum pulse width between Quadrature phase inputs.

I^2C

Table 16. Fixed I^2C DC Specifications

(Guaranteed by Characterization)

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID149	I_{I2C1}	Block current consumption at 100 kHz	–	10.5	55	µA	
SID150	I_{I2C2}	Block current consumption at 400 kHz	–	–	135	µA	
SID151	I_{I2C3}	Block current consumption at 1 Mbps	–	–	310	µA	
SID152	I_{I2C4}	I^2C enabled in Deep Sleep mode	–	–	1.4	µA	

Table 17. Fixed I^2C AC Specifications

(Guaranteed by Characterization)

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID153	F_{I2C1}	Bit rate	–	–	1	Mbps	

LCD Direct Drive

Table 18. LCD Direct Drive DC Specifications

(Guaranteed by Characterization)

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID154	I_{LCDLOW}	Operating current in low power mode	–	5	–	µA	16 × 4 small segment disp. at 50 Hz
SID155	C_{LCDCAP}	LCD capacitance per segment/common driver	–	500	5000	pF	Guaranteed by Design
SID156	LCD_{OFFSET}	Long-term segment offset	–	20	–	mV	
SID157	I_{LCDOP1}	PWM Mode current. 5-V bias. 24-MHz IMO	–	0.6	–	mA	32 × 4 segments. 50 Hz, 25 °C
SID158	I_{LCDOP2}	PWM Mode current. 3.3-V bias. 24-MHz IMO.	–	0.5	–	mA	32 × 4 segments. 50 Hz, 25 °C

Table 19. LCD Direct Drive AC Specifications

(Guaranteed by Characterization)

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID159	F_{LCD}	LCD frame rate	10	50	150	Hz	

Table 20. Fixed UART DC Specifications

(Guaranteed by Characterization)

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID160	I_{UART1}	Block current consumption at 100 Kbits/sec	–	9	55	µA	
SID161	I_{UART2}	Block current consumption at 1000 Kbits/sec	–	–	312	µA	

Table 21. Fixed UART AC Specifications

(Guaranteed by Characterization)

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID162	F_{UART}	Bit rate	–	–	1	Mbps	

SPI Specifications

Table 22. Fixed SPI DC Specifications

(Guaranteed by Characterization)

Spec ID	Parameter	Description	Min	Typ	Max	Units
SID163	I_{SPI1}	Block current consumption at 1 Mbits/sec	–	–	360	µA
SID164	I_{SPI2}	Block current consumption at 4 Mbits/sec	–	–	560	µA
SID165	I_{SPI3}	Block current consumption at 8 Mbits/sec	–	–	600	µA

Table 23. Fixed SPI AC Specifications

(Guaranteed by Characterization)

Spec ID	Parameter	Description	Min	Typ	Max	Units
SID166	F_{SPI}	SPI operating frequency (master; 6X oversampling)	–	–	8	MHz

Table 24. Fixed SPI Master Mode AC Specifications

(Guaranteed by Characterization)

Spec ID	Parameter	Description	Min	Typ	Max	Units
SID167	T_{DMO}	MOSI valid after Sclock driving edge	–	–	15	ns
SID168	T_{DSI}	MISO valid before Sclock capturing edge. Full clock, late MISO Sampling used	20	–	–	ns
SID169	T_{HMO}	Previous MOSI data hold time with respect to capturing edge at Slave	0	–	–	ns

Table 25. Fixed SPI Slave mode AC Specifications

(Guaranteed by Characterization)

Spec ID	Parameter	Description	Min	Typ	Max	Units
SID170	T_{DMI}	MOSI valid before Sclock capturing edge	40	–	–	ns
SID171	T_{DSO}	MISO valid after Sclock driving edge	–	–	$42 + 3 \times F_{CPU}$	ns
SID171A	T_{DSO_ext}	MISO valid after Sclock driving edge in Ext. Clock mode	–	–	48	ns
SID172	T_{HSO}	Previous MISO data hold time	0	–	–	ns
SID172A	$T_{SSELSCK}$	SSEL Valid to first SCK Valid edge	100	–	–	ns

Memory

Table 26. Flash DC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID173	V_{PE}	Erase and program voltage	1.71	–	5.5	V	

Table 27. Flash AC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID174	$T_{ROWWRITE}$	Row (block) write time (erase and program)	–	–	20	ms	Row (block) = 256 bytes
SID175	$T_{ROWERASE}$	Row erase time	–	–	13	ms	
SID176	$T_{ROWPROGRAM}$	Row program time after erase	–	–	7	ms	
SID178	$T_{BULKERASE}$	Bulk erase time (128 KB)	–	–	35	ms	
SID180	$T_{DEVPROG}$	Total device program time	–	–	15	seconds	Guaranteed by characterization
SID181	F_{END}	Flash endurance	100 K	–	–	cycles	Guaranteed by characterization
SID182	F_{RET}	Flash retention. $T_A \leq 55$ °C, 100 K P/E cycles	20	–	–	years	Guaranteed by characterization
SID182A		Flash retention. $T_A \leq 85$ °C, 10 K P/E cycles	10	–	–	years	Guaranteed by characterization

System Resources

Power-on-Reset (POR) with Brown Out

Table 28. Imprecise Power On Reset (PRES)

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID185	$V_{RISEIPOR}$	Rising trip voltage	0.80	–	1.45	V	Guaranteed by characterization
SID186	$V_{FALLIPOR}$	Falling trip voltage	0.75	–	1.4	V	Guaranteed by characterization
SID187	$V_{IPORHYST}$	Hysteresis	15	–	200	mV	Guaranteed by characterization

Table 29. Precise Power On Reset (POR)

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID190	$V_{FALLPPOR}$	BOD trip voltage in active and sleep modes	1.64	–	–	V	Guaranteed by characterization
SID192	$V_{FALLDPSLP}$	BOD trip voltage in Deep Sleep	1.4	–	–	V	Guaranteed by characterization

Voltage Monitors

Table 30. Voltage Monitors DC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID195	V_{LVI1}	LVI_A/D_SEL[3:0] = 0000b	1.71	1.75	1.79	V	
SID196	V_{LVI2}	LVI_A/D_SEL[3:0] = 0001b	1.76	1.80	1.85	V	
SID197	V_{LVI3}	LVI_A/D_SEL[3:0] = 0010b	1.85	1.90	1.95	V	
SID198	V_{LVI4}	LVI_A/D_SEL[3:0] = 0011b	1.95	2.00	2.05	V	
SID199	V_{LVI5}	LVI_A/D_SEL[3:0] = 0100b	2.05	2.10	2.15	V	
SID200	V_{LVI6}	LVI_A/D_SEL[3:0] = 0101b	2.15	2.20	2.26	V	
SID201	V_{LVI7}	LVI_A/D_SEL[3:0] = 0110b	2.24	2.30	2.36	V	
SID202	V_{LVI8}	LVI_A/D_SEL[3:0] = 0111b	2.34	2.40	2.46	V	
SID203	V_{LVI9}	LVI_A/D_SEL[3:0] = 1000b	2.44	2.50	2.56	V	
SID204	V_{LVI10}	LVI_A/D_SEL[3:0] = 1001b	2.54	2.60	2.67	V	
SID205	V_{LVI11}	LVI_A/D_SEL[3:0] = 1010b	2.63	2.70	2.77	V	
SID206	V_{LVI12}	LVI_A/D_SEL[3:0] = 1011b	2.73	2.80	2.87	V	
SID207	V_{LVI13}	LVI_A/D_SEL[3:0] = 1100b	2.83	2.90	2.97	V	
SID208	V_{LVI14}	LVI_A/D_SEL[3:0] = 1101b	2.93	3.00	3.08	V	
SID209	V_{LVI15}	LVI_A/D_SEL[3:0] = 1110b	3.12	3.20	3.28	V	
SID210	V_{LVI16}	LVI_A/D_SEL[3:0] = 1111b	4.39	4.50	4.61	V	
SID211	LVI_IDD	Block current	–	–	100	µA	Guaranteed by characterization

Table 31. Voltage Monitors AC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID212	$T_{MONTRIP}$	Voltage monitor trip time	–	–	1	µs	Guaranteed by characterization

Table 36. ILO AC Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID234	$T_{STARTILO1}$	ILO startup time	–	–	2	ms	Guaranteed by characterization
SID236	$T_{ILODUTY}$	ILO duty cycle	40	50	60	%	Guaranteed by characterization
SID237	$F_{ILOTRIM1}$	32 kHz trimmed frequency	15	32	50	kHz	±60% with trim.

Table 37. PLL DC Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID410	IDD_PLL_48	In = 3 MHz, Out = 48 MHz	–	530	610	µA	
SID411	IDD_PLL_24	In = 3 MHz, Out = 24 MHz	–	300	405	µA	

Table 38. PLL AC Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID412	F_{PLLIN}	PLL input frequency	1	–	48	MHz	
SID413	F_{PLLINT}	PLL intermediate frequency; prescaler out	1	–	3	MHz	
SID414	F_{PLLVCO}	VCO output frequency before post-divide	22.5	–	104	MHz	
SID415	D_{IVVCO}	VCO Output post-divider range; PLL output frequency is F_{PPLVCO}/D_{IVVCO}	1	–	8	–	
SID416	PLLlocktime	Lock time at startup	–	–	250	us	
SID417	Jperiod_1	Period jitter for VCO ≥ 67 MHz	–	–	150	ps	Guaranteed By Design
SID416A	Jperiod_2	Period jitter for VCO ≤ 67 MHz	–	–	200	ps	Guaranteed By Design

Table 39. External Clock Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID305	ExtClkFreq	External Clock input Frequency	0	–	48	MHz	Guaranteed by characterization
SID306	ExtClkDuty	Duty cycle; Measured at $V_{DD/2}$	45	–	55	%	Guaranteed by characterization

Table 40. Watch Crystal Oscillator (WCO) Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details / Conditions
IMO WCO-PLL calibrated mode							
SID330	IMOWCO1	Frequency variation with IMO set to 3 MHz	–0.6	–	0.6	%	Does not include WCO tolerance
SID331	IMOWCO2	Frequency variation with IMO set to 5 MHZ	–0.4	–	0.4	%	Does not include WCO tolerance
SID332	IMOWCO3	Frequency variation with IMO set to 7 or 9 MHZ	–0.3	–	0.3	%	Does not include WCO tolerance
SID333	IMOWCO4	All other IMO frequency settings	–0.2	–	0.2	%	Does not include WCO tolerance

Table 40. Watch Crystal Oscillator (WCO) Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details / Conditions
WCO Specifications							
SID398	FWCO	Crystal frequency	–	32.768	–	kHz	
SID399	FTOL	Frequency tolerance	–	50	250	ppm	With 20-ppm crystal.
SID400	ESR	Equivalent series resistance	–	50	–	kΩ	
SID401	PD	Drive Level	–	–	1	µW	
SID402	TSTART	Startup time	–	–	500	ms	
SID403	CL	Crystal load capacitance	6	–	12.5	pF	
SID404	C0	Crystal shunt capacitance	–	1.35	–	pF	
SID405	IWCO1	Operating current (high power mode)	–	–	8	uA	

Table 41. External Crystal Oscillator (ECO) Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID316	IECO1	Block operating current	–	–	1.5	mA	
SID317	FECO	Crystal frequency range	4	–	33	MHz	

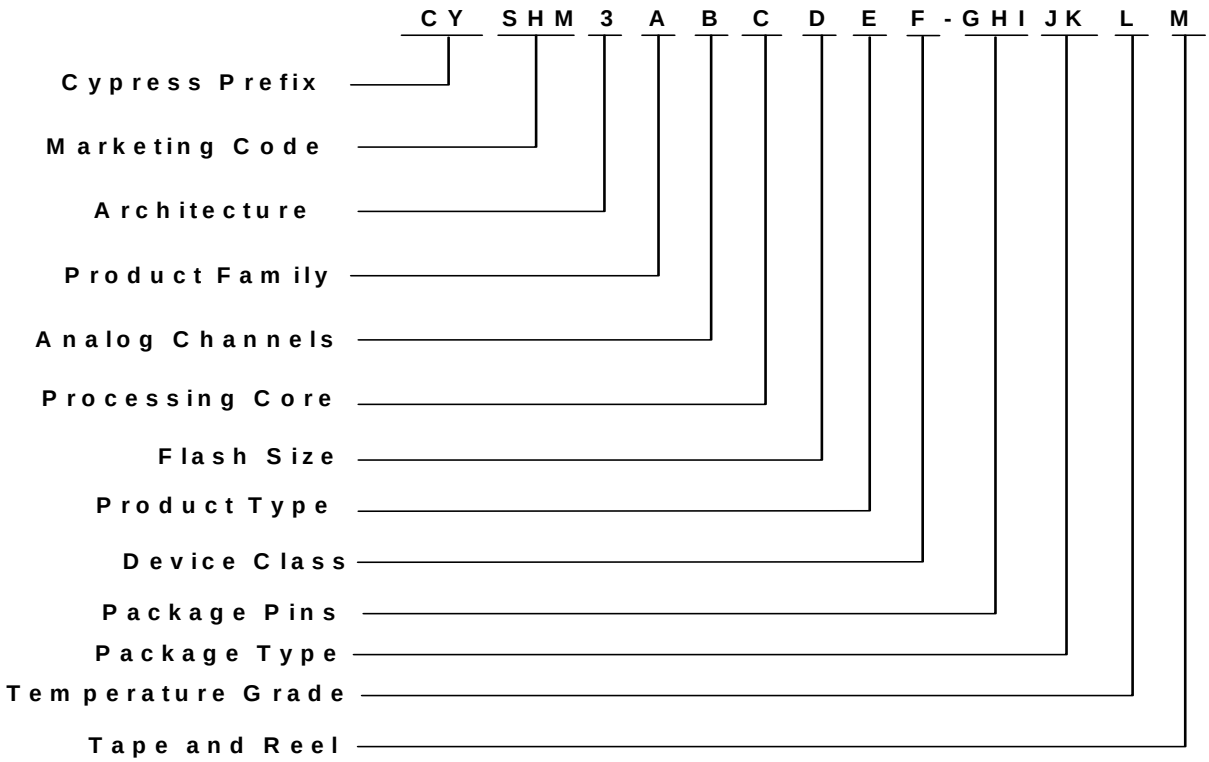
Table 42. UDB AC Specifications

(Guaranteed by Characterization)

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
Datapath performance							
SID249	$F_{MAX-TIMER}$	Max frequency of 16-bit timer in a UDB pair	–	–	48	MHz	
SID250	$F_{MAX-ADDER}$	Max frequency of 16-bit adder in a UDB pair	–	–	48	MHz	
SID251	F_{MAX_CRC}	Max frequency of 16-bit CRC/PRS in a UDB pair	–	–	48	MHz	
PLD Performance in UDB							
SID252	F_{MAX_PLD}	Max frequency of 2-pass PLD function in a UDB pair	–	–	48	MHz	
Clock to Output Performance							
SID253	$T_{CLK\_OUT\_UDB1}$	Prop. delay for clock in to data out at 25 °C, Typ.	–	15	–	ns	
SID254	$T_{CLK\_OUT\_UDB2}$	Prop. delay for clock in to data out, Worst case.	–	25	–	ns	

Part Numbering Conventions

The part number fields are defined as follows.



Acronyms

Table 53. Acronyms Used in this Document

Acronym	Description
abus	analog local bus
ADC	analog-to-digital converter
AG	analog global
AHB	AMBA (advanced microcontroller bus architecture) high-performance bus, an ARM data transfer bus
ALU	arithmetic logic unit
AMUXBUS	analog multiplexer bus
API	application programming interface
APSR	application program status register
ARM®	advanced RISC machine, a CPU architecture
ATM	automatic thump mode
BW	bandwidth
CAN	Controller Area Network, a communications protocol
CMRR	common-mode rejection ratio
CPU	central processing unit
CRC	cyclic redundancy check, an error-checking protocol
DAC	digital-to-analog converter, see also IDAC, VDAC
DFB	digital filter block
DIO	digital input/output, GPIO with only digital capabilities, no analog. See GPIO.
DMIPS	Dhrystone million instructions per second
DMA	direct memory access, see also TD
DNL	differential nonlinearity, see also INL
DNU	do not use
DR	port write data registers
DSI	digital system interconnect
DWT	data watchpoint and trace
ECC	error correcting code
ECO	external crystal oscillator
EEPROM	electrically erasable programmable read-only memory
EMI	electromagnetic interference
EMIF	external memory interface
EOC	end of conversion
EOF	end of frame
EPSR	execution program status register
ESD	electrostatic discharge

Table 53. Acronyms Used in this Document *(continued)*

Acronym	Description
ETM	embedded trace macrocell
FIR	finite impulse response, see also IIR
FPB	flash patch and breakpoint
FS	full-speed
GPIO	general-purpose input/output, applies to a PSoC pin
HVI	high-voltage interrupt, see also LVI, LVD
IC	integrated circuit
IDAC	current DAC, see also DAC, VDAC
IDE	integrated development environment
I^2C, or IIC	Inter-Integrated Circuit, a communications protocol
IIR	infinite impulse response, see also FIR
ILO	internal low-speed oscillator, see also IMO
IMO	internal main oscillator, see also ILO
INL	integral nonlinearity, see also DNL
I/O	input/output, see also GPIO, DIO, SIO, USBIO
IPOR	initial power-on reset
IPSR	interrupt program status register
IRQ	interrupt request
ITM	instrumentation trace macrocell
LCD	liquid crystal display
LIN	Local Interconnect Network, a communications protocol.
LR	link register
LUT	lookup table
LVD	low-voltage detect, see also LVI
LVI	low-voltage interrupt, see also HVI
LVTTL	low-voltage transistor-transistor logic
MAC	multiply-accumulate
MCU	microcontroller unit
MISO	master-in slave-out
NC	no connect
NMI	nonmaskable interrupt
NRZ	non-return-to-zero
NVIC	nested vectored interrupt controller
NVL	nonvolatile latch, see also WOL
opamp	operational amplifier
PAL	programmable array logic, see also PLD

Table 53. Acronyms Used in this Document *(continued)*

Acronym	Description
PC	program counter
PCB	printed circuit board
PGA	programmable gain amplifier
PHUB	peripheral hub
PHY	physical layer
PICU	port interrupt control unit
PLA	programmable logic array
PLD	programmable logic device, see also PAL
PLL	phase-locked loop
PMDD	package material declaration data sheet
POR	power-on reset
PRES	precise power-on reset
PRS	pseudo random sequence
PS	port read data register
PSoC®	Programmable System-on-Chip™
PSRR	power supply rejection ratio
PWM	pulse-width modulator
RAM	random-access memory
RISC	reduced-instruction-set computing
RMS	root-mean-square
RTC	real-time clock
RTL	register transfer language
RTR	remote transmission request
RX	receive
SAR	successive approximation register
SC/CT	switched capacitor/continuous time
SCL	I^2C serial clock
SDA	I^2C serial data
S/H	sample and hold
SINAD	signal to noise and distortion ratio
SIO	special input/output, GPIO with advanced features. See GPIO.
SOC	start of conversion
SOF	start of frame
SPI	Serial Peripheral Interface, a communications protocol
SR	slew rate
SRAM	static random access memory
SRES	software reset
SWD	serial wire debug, a test protocol

Table 53. Acronyms Used in this Document *(continued)*

Acronym	Description
SWV	single-wire viewer
TD	transaction descriptor, see also DMA
THD	total harmonic distortion
TIA	transimpedance amplifier
TRM	technical reference manual
TTL	transistor-transistor logic
TX	transmit
UART	Universal Asynchronous Transmitter Receiver, a communications protocol
UDB	universal digital block
USB	Universal Serial Bus
USBIO	USB input/output, PSoC pins used to connect to a USB port
VDAC	voltage DAC, see also DAC, IDAC
WDT	watchdog timer
WOL	write once latch, see also NVL
WRES	watchdog timer reset
XRES	external reset I/O pin
XTAL	crystal